

MOSFET

OptiMOS™3 Power-Transistor, 200 V

Features

- N-channel, normal level
- 175 °C rated
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Ideal for high-frequency switching and synchronous rectification

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

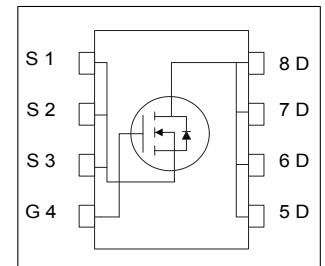
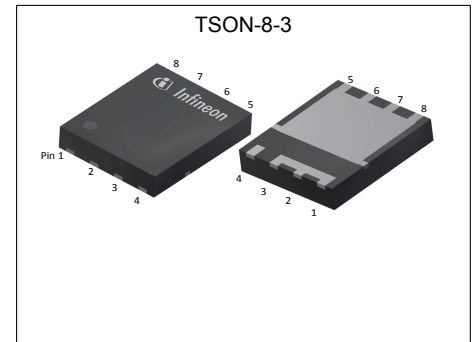


Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|------------------|-------|------|
| V_{DS} | 200 | V |
| $R_{DS(on),max}$ | 22 | mΩ |
| I_D | 52 | A |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|----------|---------|---------------|
| BSC220N20NSFD | TSON-8-3 | 220N20F | - |

Table of Contents

| | |
|---|----|
| Description | 1 |
| Maximum ratings | 3 |
| Thermal characteristics | 3 |
| Electrical characteristics | 4 |
| Electrical characteristics diagrams | 6 |
| Package Outlines | 10 |
| Revision History | 11 |
| Trademarks | 11 |
| Disclaimer | 11 |

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------------------------|-------------------|--------|------|----------|-------------|--|
| | | Min. | Typ. | Max. | | |
| Continuous drain current | I_D | - | - | 52 41 | A | $T_C=25\text{ °C}$ $T_C=100\text{ °C}$ |
| Pulsed drain current ¹⁾ | $I_{D,pulse}$ | - | - | 208 | A | $T_C=25\text{ °C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 214 | mJ | $I_D=38\text{ A}$, $R_{GS}=25\text{ }\Omega$ |
| Reverse diode peak dv/dt | dv/dt | - | - | 60 | kV/ μ s | $I_D=52\text{ A}$, $V_{DS}=100\text{ V}$, $di/dt=1500\text{ A}/\mu\text{s}$, $T_{j,max}=175\text{ °C}$ |
| Gate source voltage | V_{GS} | -20 | - | 20 | V | - |
| Power dissipation | P_{tot} | - | - | 214 | W | $T_C=25\text{ °C}$ |
| Operating and storage temperature | T_j , T_{stg} | -55 | - | 175 | °C | IEC climatic category; DIN IEC 68-1: 55/175/56 |

2 Thermal characteristics

$T_j=25\text{ °C}$, unless otherwise specified

Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|-----------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | 0.4 | 0.7 | K/W | - |
| Thermal resistance, junction - ambient, minimal footprint | R_{thJA} | - | - | 75 | K/W | - |
| Thermal resistance, junction - ambient, 6 cm ² cooling area ²⁾ | R_{thJA} | - | - | 50 | K/W | - |

¹⁾ See Diagram 3

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μ m thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|-----------|----------|---------------|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 200 | - | - | V | $V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$ |
| Gate threshold voltage | $V_{GS(th)}$ | 2 | 3 | 4 | V | $V_{DS}=V_{GS}$, $I_D=137\text{ }\mu\text{A}$ |
| Zero gate voltage drain current | I_{DSS} | - | 0.1 10 | 1 100 | μA | $V_{DS}=160\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=160\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$ |
| Gate-source leakage current | I_{GSS} | - | 1 | 100 | nA | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 17.7 | 22 | m Ω | $V_{GS}=10\text{ V}$, $I_D=52\text{ A}$ |
| Gate resistance ¹⁾ | R_G | - | 3.7 | 5.5 | Ω | - |
| Transconductance | g_{fs} | 44 | 88 | - | S | $ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=52\text{ A}$ |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Input capacitance ¹⁾ | C_{iss} | - | 2770 | 3680 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$ |
| Output capacitance ¹⁾ | C_{oss} | - | 210 | 279 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$ |
| Reverse transfer capacitance ¹⁾ | C_{rss} | - | 5.7 | 10 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$ |
| Turn-on delay time | $t_{d(on)}$ | - | 7 | - | ns | $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=17\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$ |
| Rise time | t_r | - | 7 | - | ns | $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=17\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$ |
| Turn-off delay time | $t_{d(off)}$ | - | 28 | - | ns | $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=17\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$ |
| Fall time | t_f | - | 10 | - | ns | $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=17\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$ |

Table 6 Gate charge characteristics²⁾

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 13.1 | - | nC | $V_{DD}=100\text{ V}$, $I_D=52\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge ¹⁾ | Q_{gd} | - | 4.4 | 7 | nC | $V_{DD}=100\text{ V}$, $I_D=52\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Switching charge | Q_{sw} | - | 9.2 | - | nC | $V_{DD}=100\text{ V}$, $I_D=52\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total ¹⁾ | Q_g | - | 34 | 43 | nC | $V_{DD}=100\text{ V}$, $I_D=52\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate plateau voltage | $V_{plateau}$ | - | 4.7 | - | V | $V_{DD}=100\text{ V}$, $I_D=52\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Output charge ¹⁾ | Q_{oss} | - | 84 | 111 | nC | $V_{DD}=100\text{ V}$, $V_{GS}=0\text{ V}$ |

¹⁾ Defined by design. Not subject to production test.

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Diode continuous forward current | I_S | - | - | 52 | A | $T_C=25\text{ °C}$ |
| Diode pulse current ¹⁾ | $I_{S,pulse}$ | - | - | 208 | A | $T_C=25\text{ °C}$ |
| Diode hard commutation current ²⁾ | $I_{S,hard}$ | - | - | 52 | A | $T_C=25\text{ °C}$, $di_F/dt=1500\text{ A}/\mu\text{s}$ |
| Diode forward voltage | V_{SD} | - | 1.0 | 1.2 | V | $V_{GS}=0\text{ V}$, $I_F=52\text{ A}$, $T_J=25\text{ °C}$ |
| Reverse recovery time ³⁾ | t_{rr} | - | 89 | - | ns | $V_R=100\text{ V}$, $I_F=12.5\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge ³⁾ | Q_{rr} | - | 195 | - | nC | $V_R=100\text{ V}$, $I_F=12.5\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ |

¹⁾ Diode pulse current is defined by thermal and/or package limits

²⁾ Maximum allowed hard-commutated current through diode at $di/dt=1500\text{ A}/\mu\text{s}$

³⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

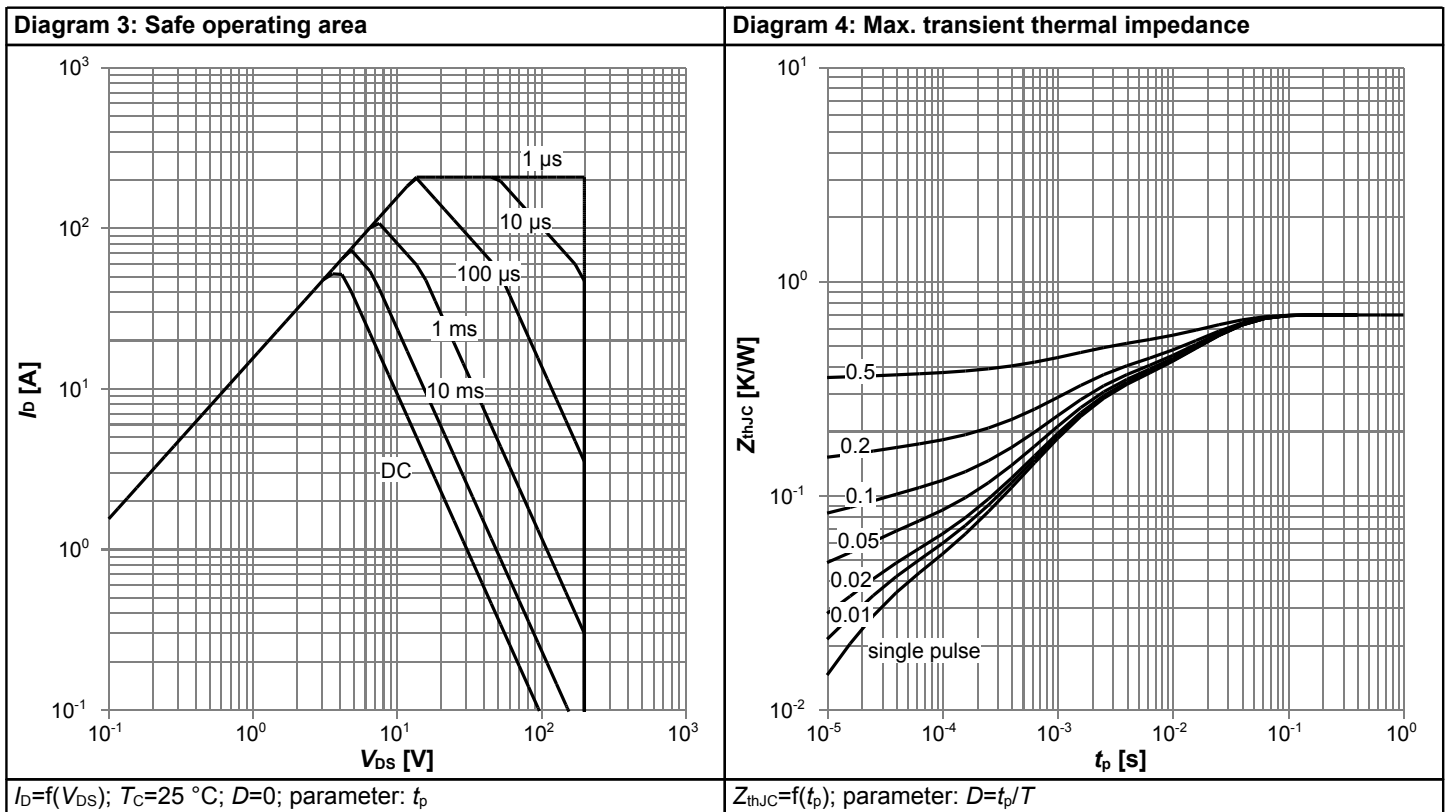
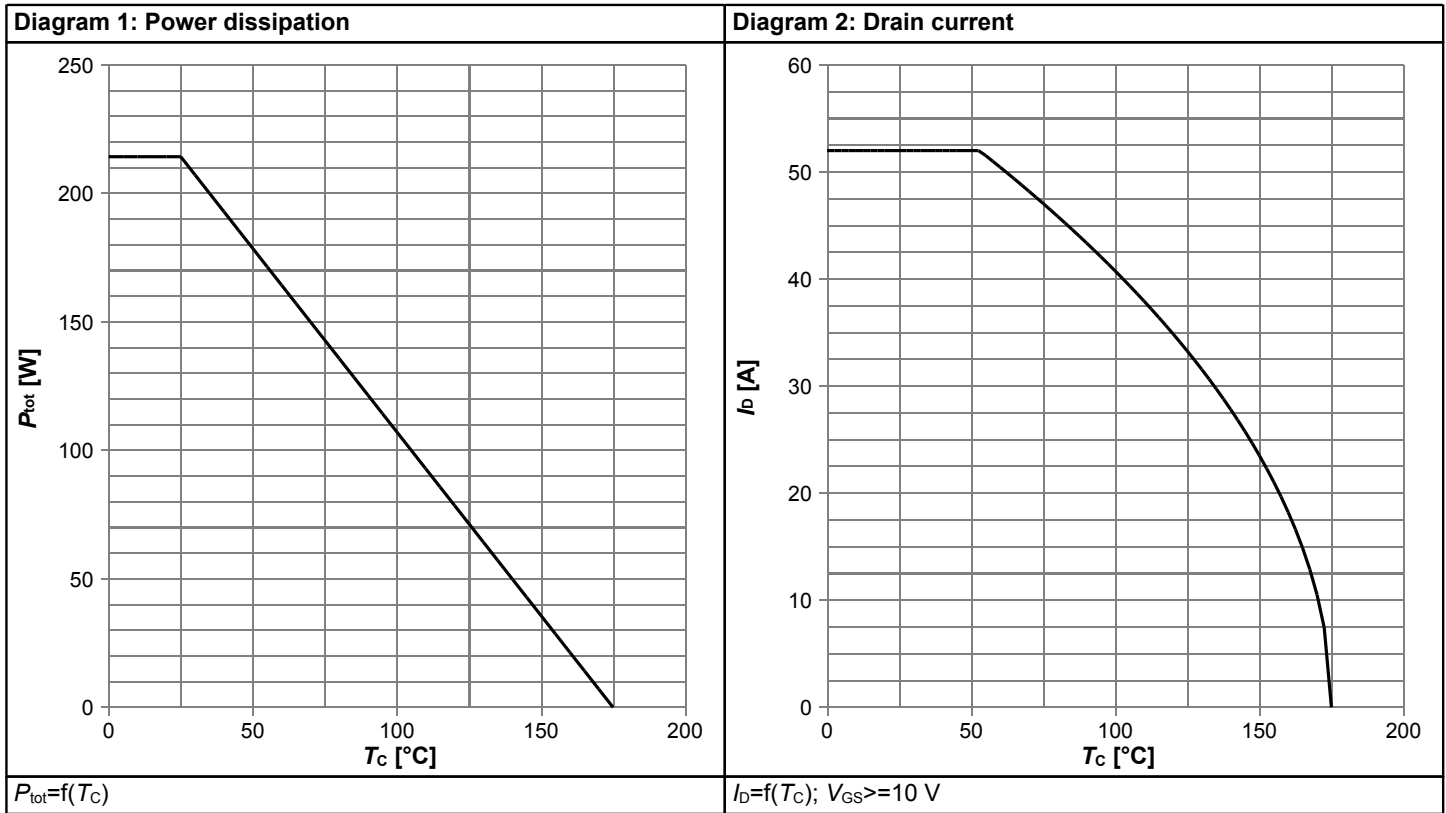
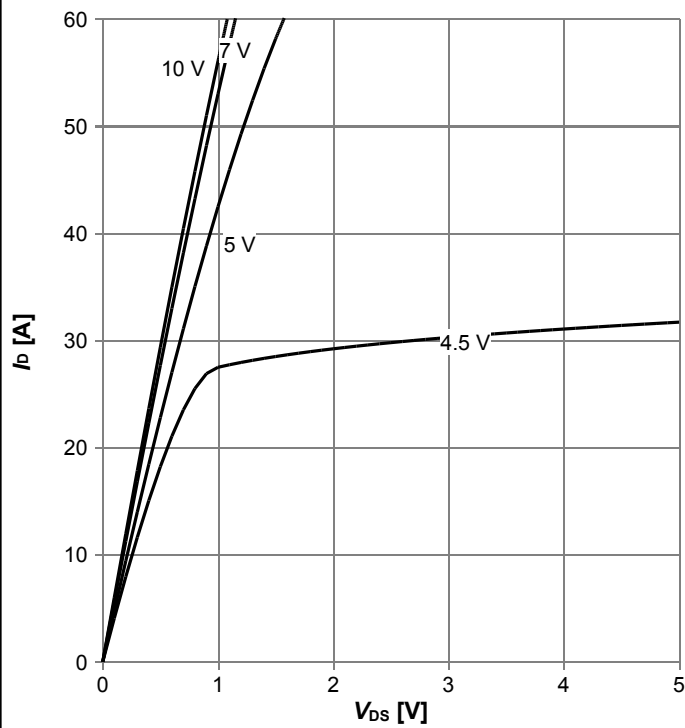
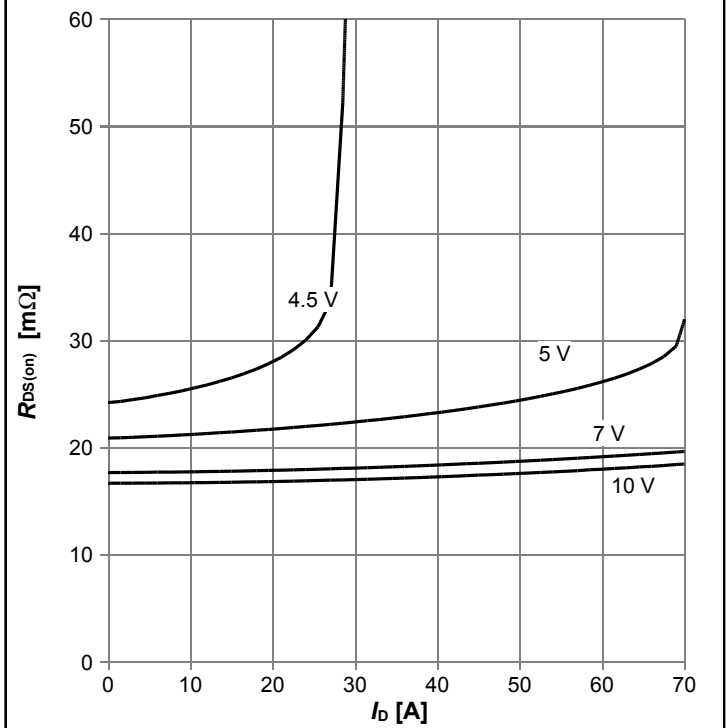


Diagram 5: Typ. output characteristics



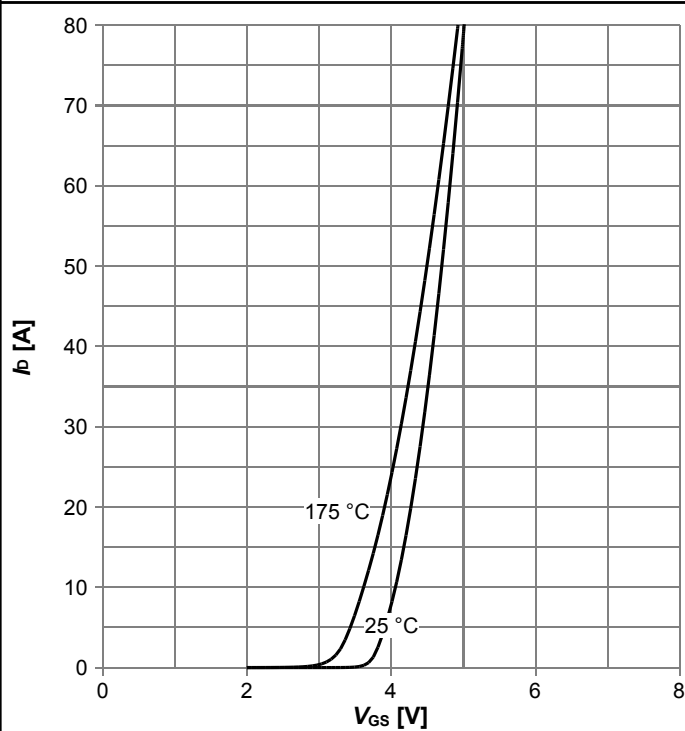
$I_D = f(V_{DS}); T_j = 25\text{ °C};$ parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



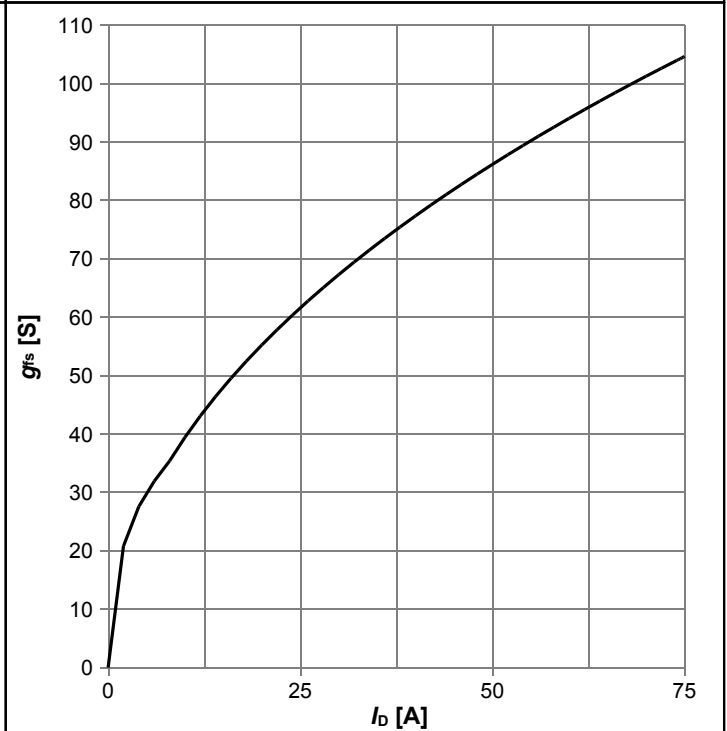
$R_{DS(on)} = f(I_D); T_j = 25\text{ °C};$ parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



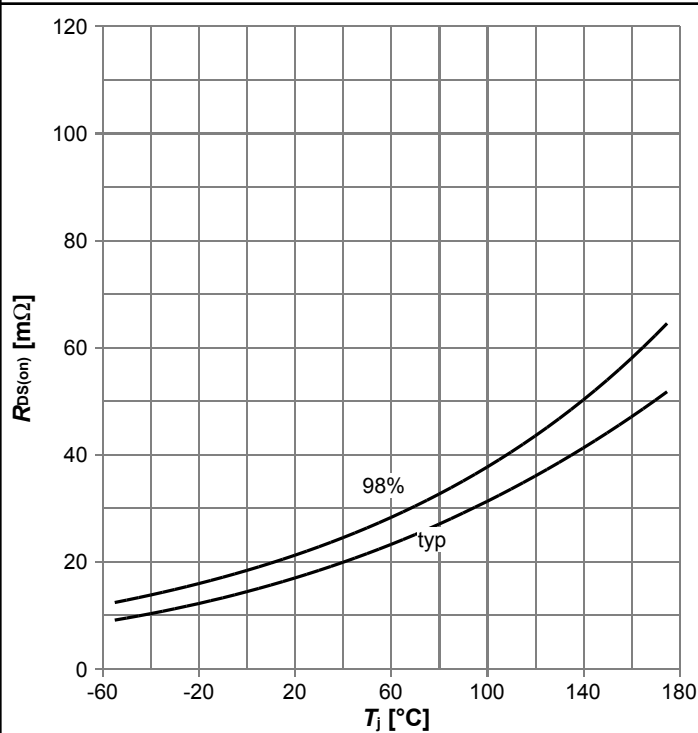
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max};$ parameter: T_j

Diagram 8: Typ. forward transconductance



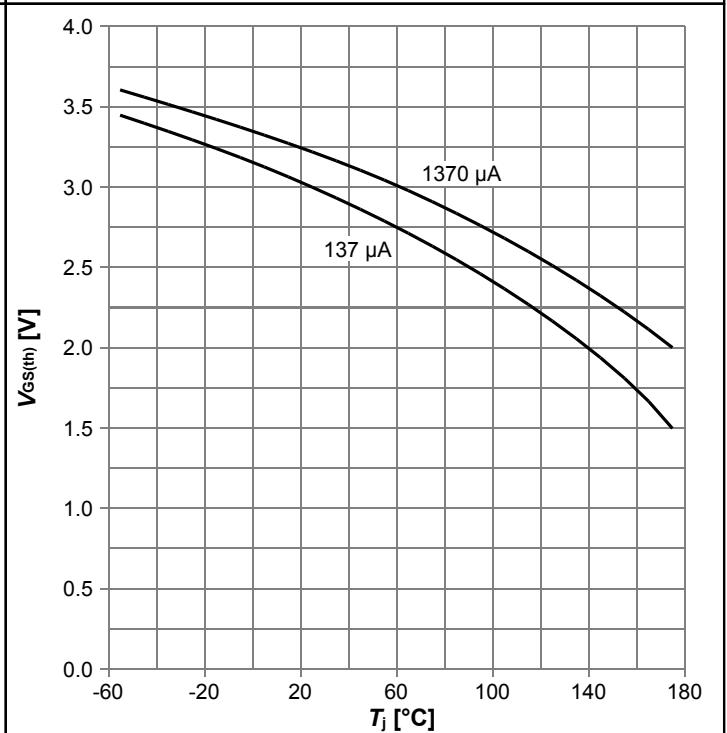
$g_{fs} = f(I_D); T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



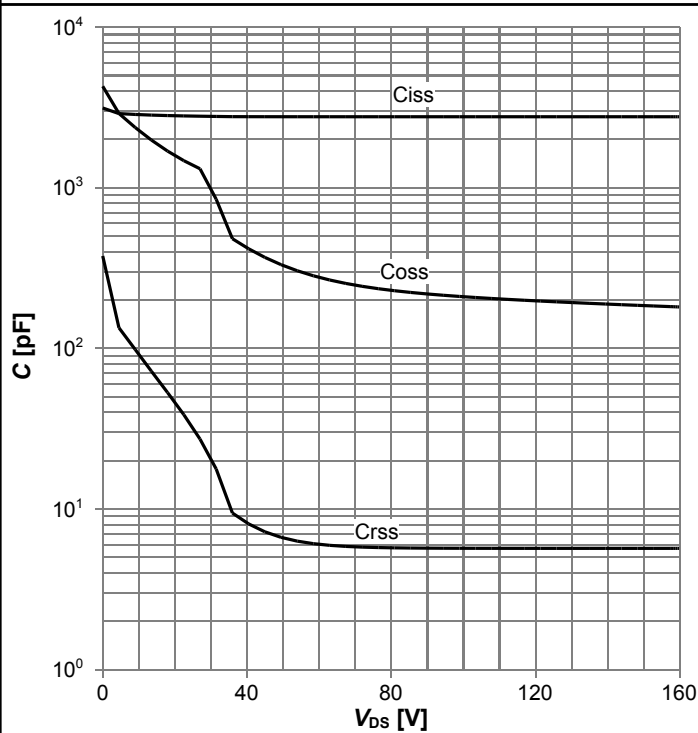
$R_{DS(on)}=f(T_j)$; $I_D=55\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



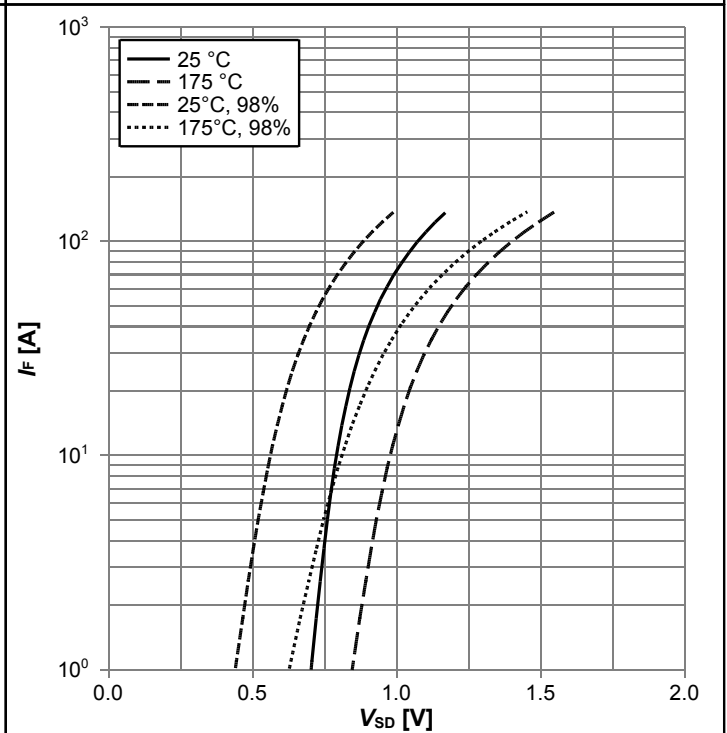
$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



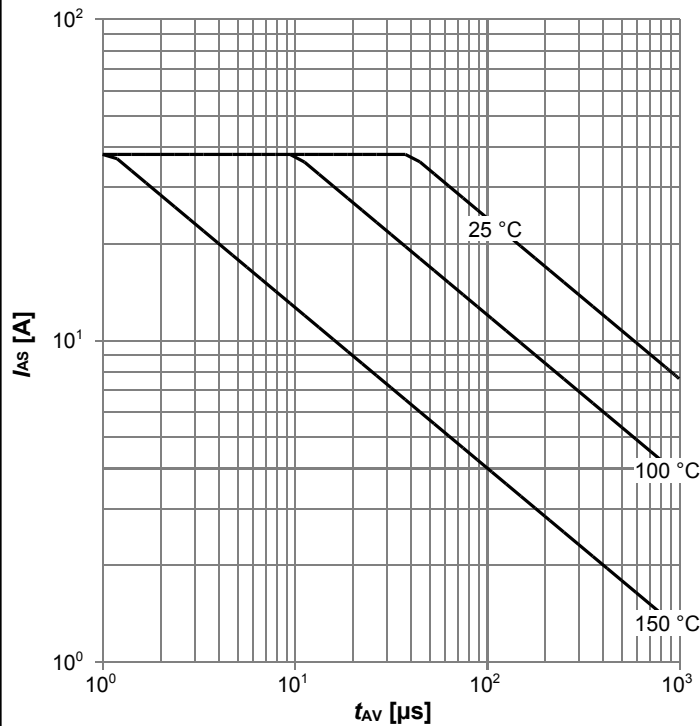
$C=f(V_{DS})$; $V_{GS}=0\text{ V}$; $f=1\text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



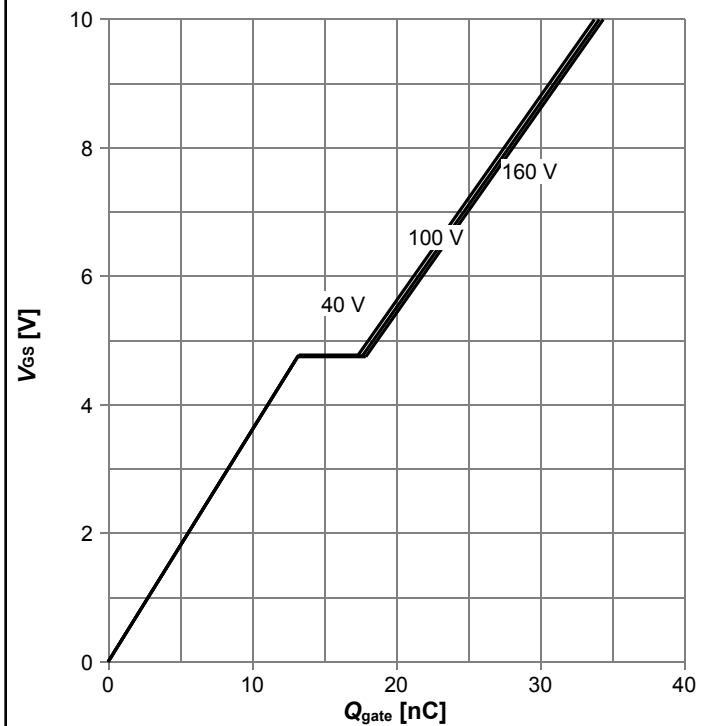
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



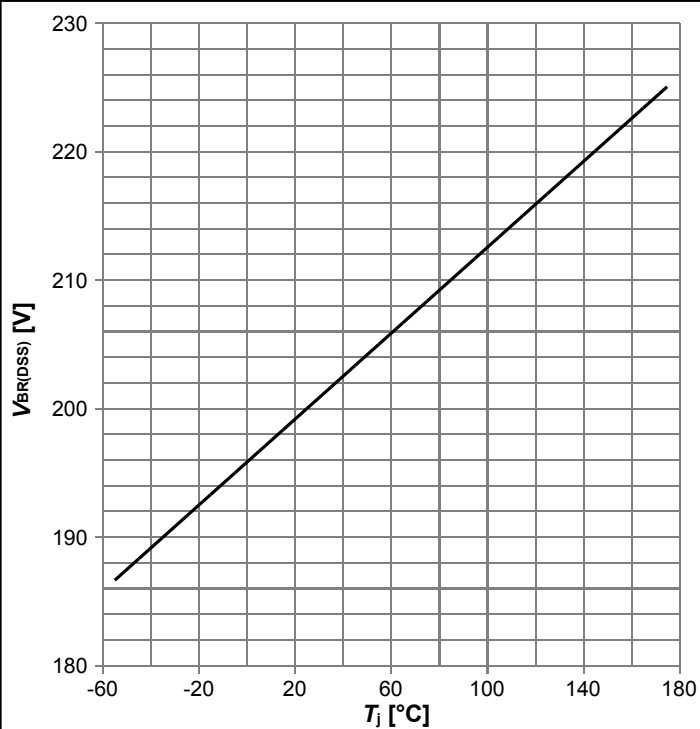
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate}); I_D=55 \text{ A pulsed}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

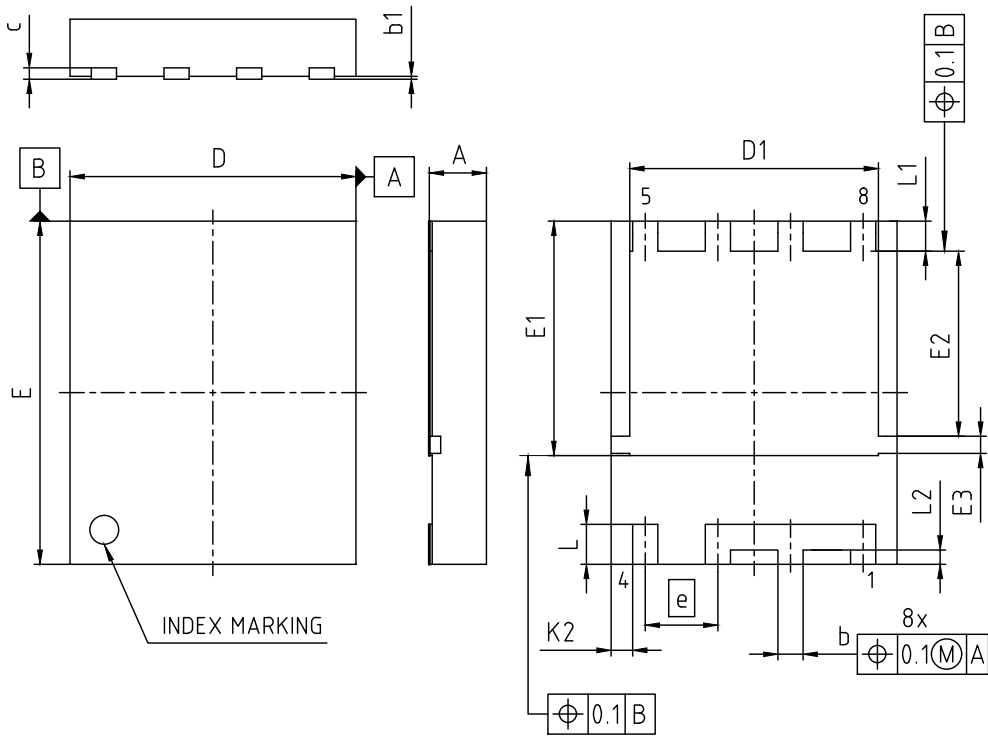


$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Diagram Gate charge waveforms



5 Package Outlines



| DIMENSION | MILLIMETERS | |
|-----------|-------------|------|
| | MIN. | MAX. |
| A | - | 1.10 |
| b | 0.34 | 0.54 |
| b1 | - | 0.05 |
| c | 0.20 | |
| D | 4.90 | 5.10 |
| D1 | 4.25 | 4.45 |
| E | 5.90 | 6.10 |
| E1 | 4.00 | 4.20 |
| E2 | 3.14 | 3.34 |
| E3 | 0.20 | 0.40 |
| e | 1.27 | |
| K2 | (0.37) | |
| L | 0.60 | 0.80 |
| L1 | 0.43 | 0.63 |
| L2 | (0.25) | |

| |
|------------------------------------|
| DOCUMENT NO. Z8B00187559 |
| REVISION 01 |
| SCALE 10:1 0 1 2mm |
| EUROPEAN PROJECTION |
| ISSUE DATE 14.12.2017 |

Figure 1 Outline TSON-8-3, dimensions in mm/inches

Revision History

BSC220N20NSFD

Revision: 2018-03-14, Rev. 2.0

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0 | 2018-03-14 | Release of final version |

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